



Description

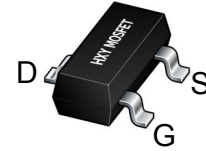
The AO3400-HXY uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

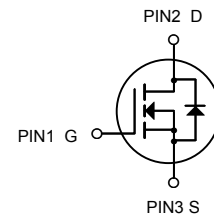
$V_{DS} = 30V, I_D = 5.8A$
 $R_{DS(ON)} < 28m\Omega @ V_{GS}=10V$
 $R_{DS(ON)} < 34m\Omega @ V_{GS}=4.5V$

Application

High power and current handing capability
Lead free product is acquired
Surface mount package
PWM applications
Load switch
Power management



SOT23-3L



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AO3400-HXY	SOT23-3L	X0VX	3000PCS

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 12	V
I_D	Drain Current-Continuous	5.8	A
I_{DM}	Drain Current-Pulsed ^(Note 1)	30	A
P_D	Maximum Power Dissipation	1.4	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient ^(Note 2)	89	$^\circ C/W$



Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	30	33	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V, V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.7	0.9	1.4	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =2.5V, I _D =4A	-	41	55	mΩ
		V _{GS} =4.5V, I _D =5A	-	23	34	mΩ
		V _{GS} =10V, I _D =5.8A	-	21	28	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =5A	10	-	-	S
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V, F=1.0MHz	-	825	-	PF
Output Capacitance	C _{oss}		-	100	-	PF
Reverse Transfer Capacitance	C _{rss}		-	78	-	PF
Turn-on Delay Time	t _{d(on)}	V _{DD} =15V, R _L =2.7Ω V _{GS} =10V, R _{GEN} =3Ω	-	3.3	-	nS
Turn-on Rise Time	t _r		-	4.8	-	nS
Turn-Off Delay Time	t _{d(off)}		-	26	-	nS
Turn-Off Fall Time	t _f		-	4	-	nS
Total Gate Charge	Q _g	V _{DS} =15V, I _D =5.8A, V _{GS} =4.5V	-	10	-	nC
Gate-Source Charge	Q _{gs}		-	1.6	-	nC
Gate-Drain Charge	Q _{gd}		-	3.1	-	nC
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V, I _S =5.8A	-	-	1.2	V
Diode Forward Current ^(Note 2)	I _S		-	-	5.8	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

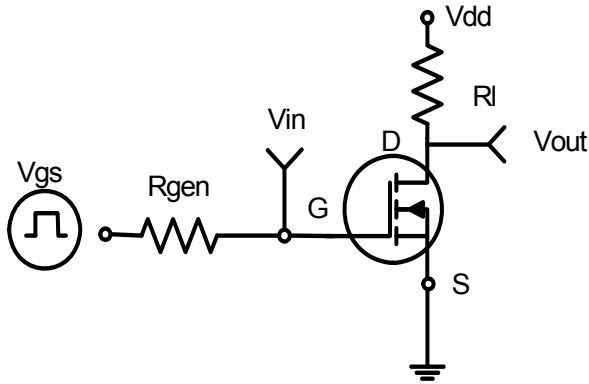


Figure 1: Switching Test Circuit

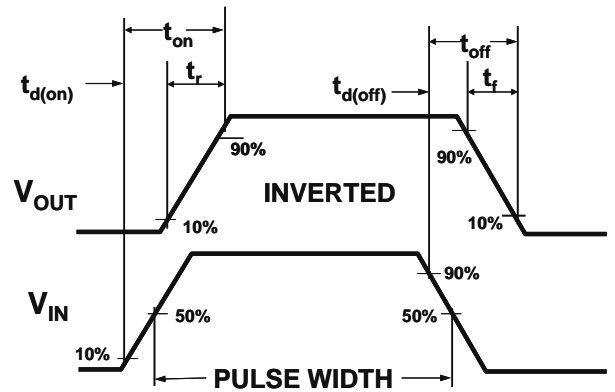


Figure 2: Switching Waveforms

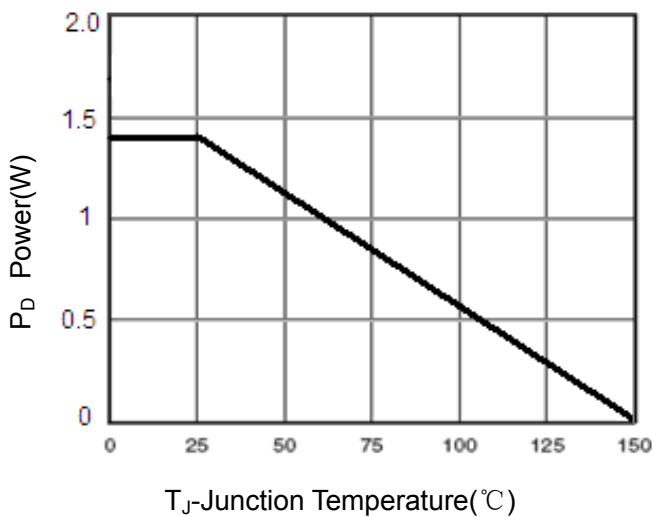


Figure 3 Power Dissipation

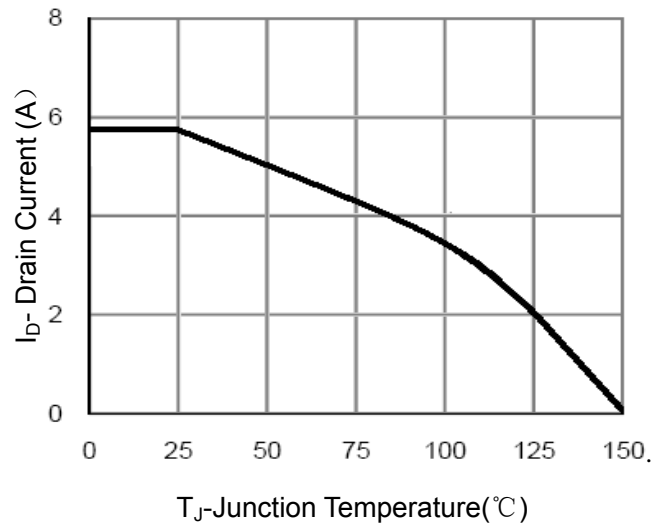


Figure 4 Drain Current

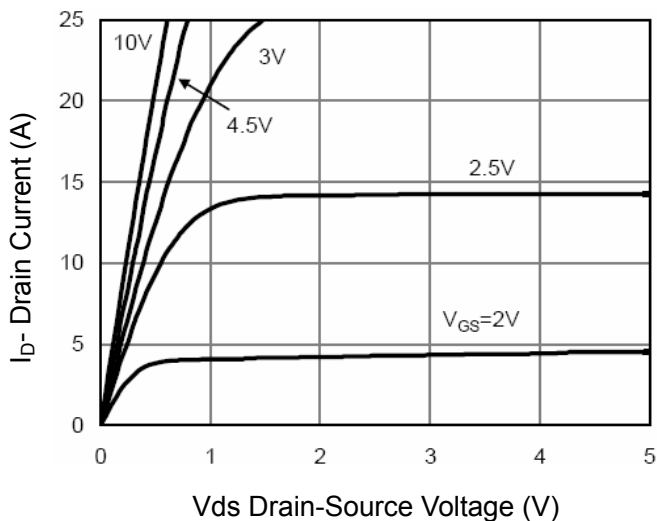


Figure 5 Output Characteristics

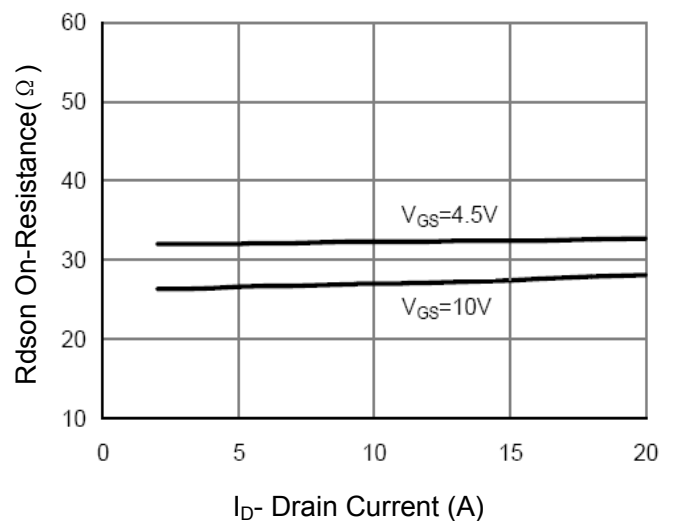


Figure 6 Drain-Source On-Resistance

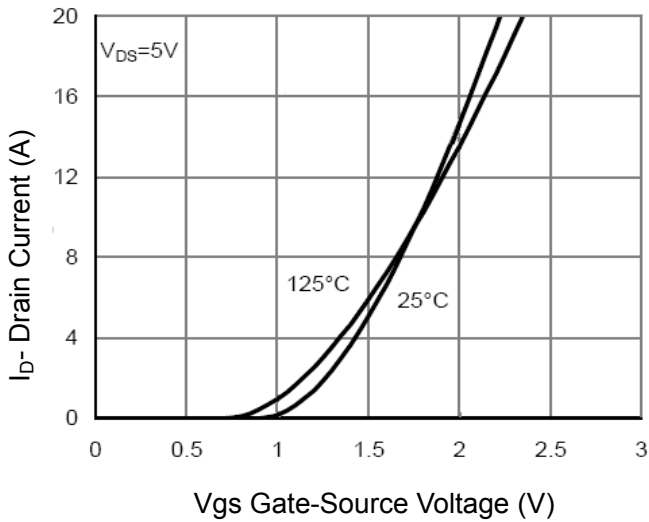


Figure 7 Transfer Characteristics

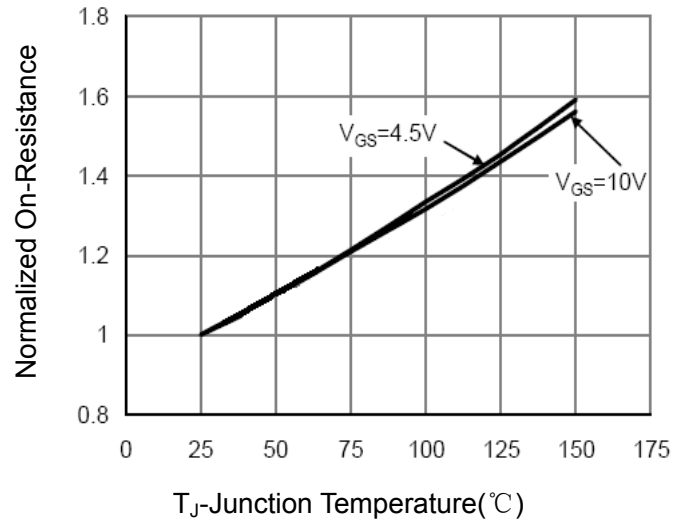


Figure 8 Drain-Source On-Resistance

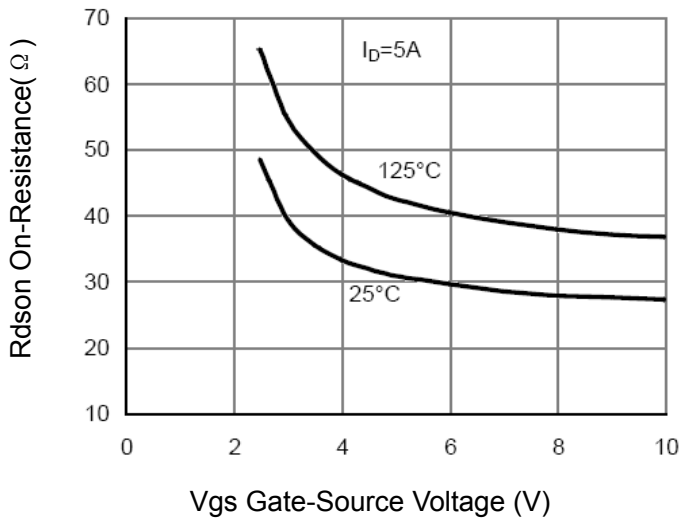


Figure 9 Rdson vs V_{GS}

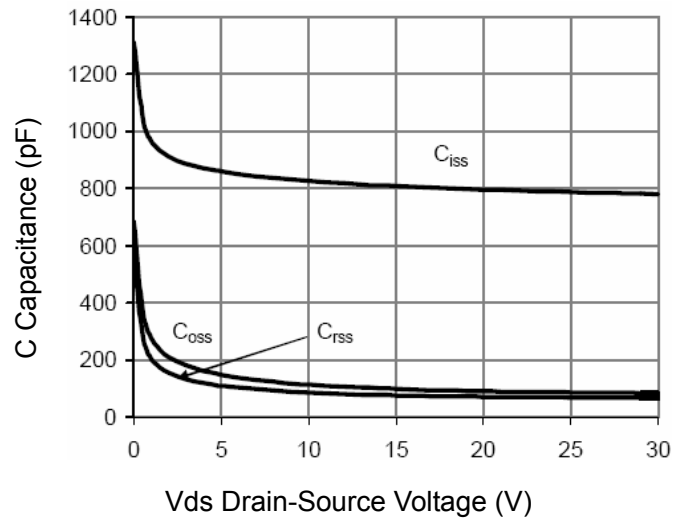


Figure 10 Capacitance vs V_{ds}

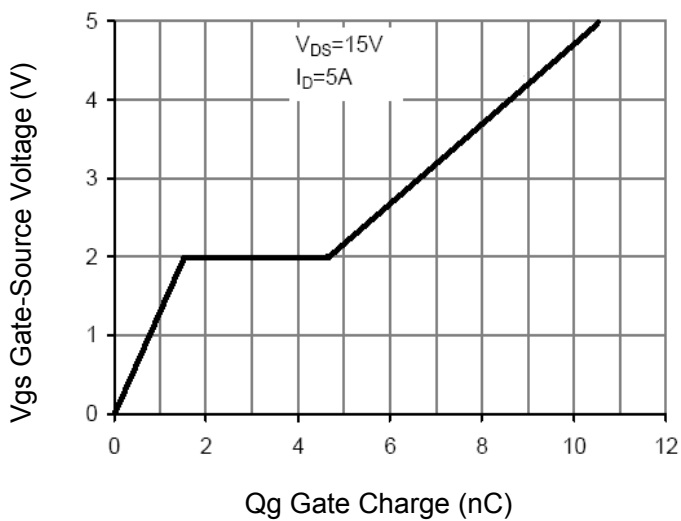


Figure 11 Gate Charge

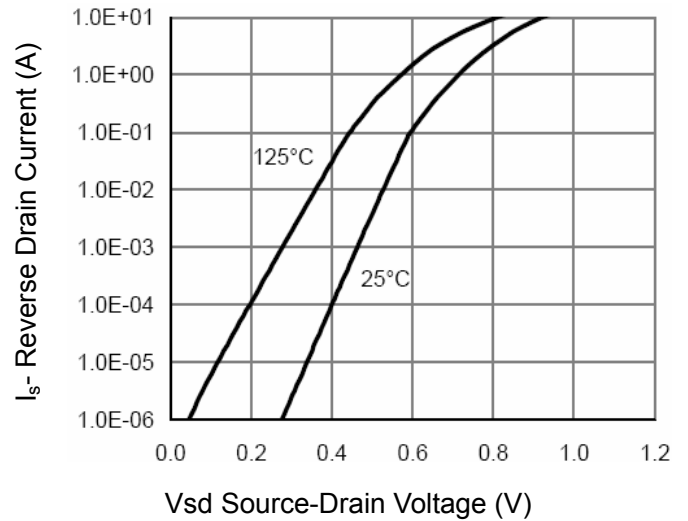


Figure 12 Source- Drain Diode Forward

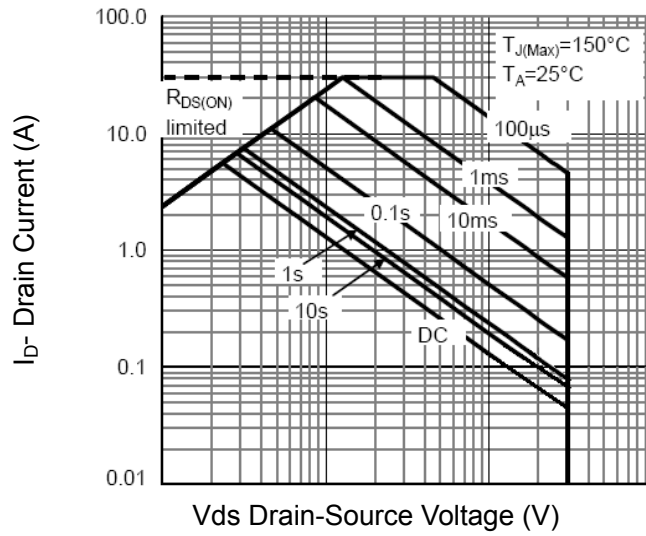


Figure 13 Safe Operation Area

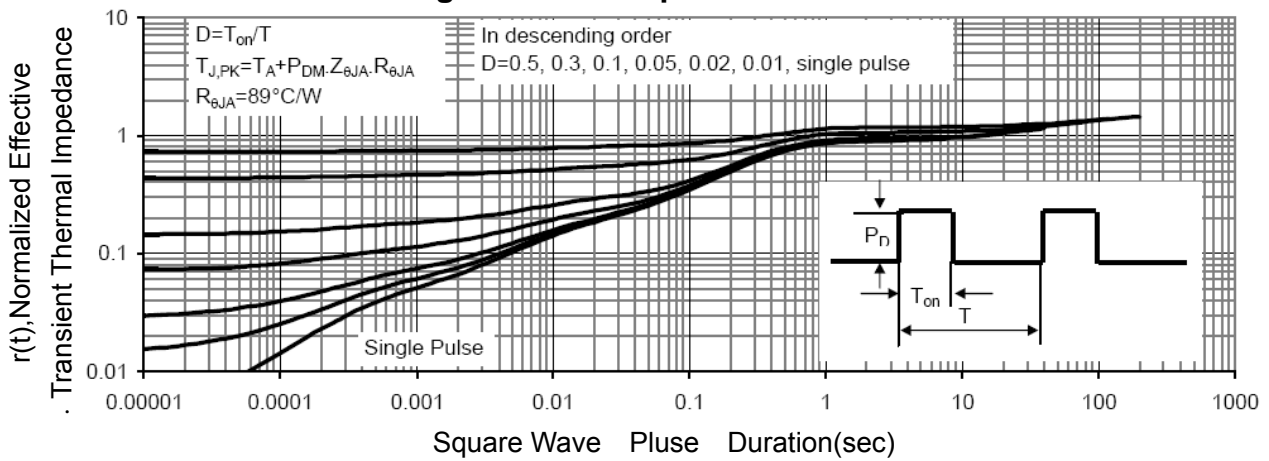
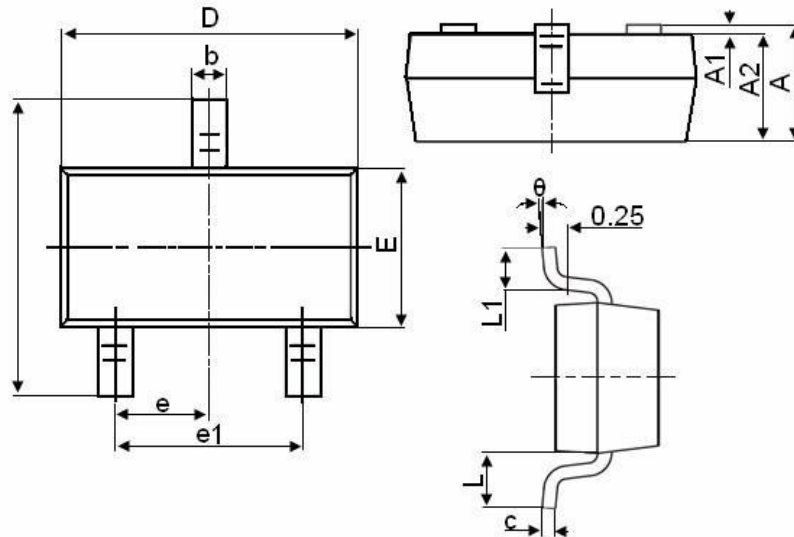


Figure 14 Normalized Maximum Transient Thermal Impedance



SOT23-3L Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	1.050	1.250
A1	0.000	0.100
A2	1.050	1.150
b	0.300	0.500
c	0.100	0.200
D	2.800	3.000
E	1.500	1.700
E1	2.650	2.950
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.600
θ	0°	8°

